



SANYO Semiconductors

# DATA SHEET

## LA6560 — Monolithic Linear IC For CD Five-Channel Driver (BTL : Four-Channel, H Bridge : One-Channel)

### Overview

The LA6560 is a 5-channel driver (BTL : 4-channel, H bridge : 1-channel) for CD players.

### Functions

- Power amplifier 5-channel built-in. (Bridge-connection (BTL) : 4-channel, H bridge : 1-channel)
- $I_O$  max 1A
- Level shift circuit built-in (except H bridge).
- Mute circuit (output ON/OFF) built-in.  
(Operable with BTL AMP and not operable for the H bridge of 5VREG)
- 5V regulator built-in (external PNP transistor).
- With VREF changeover function (H : external, L : internal (2.5V) selected)
- Overheat protection circuit (thermal shutdown) built-in.

### Specifications

**Maximum Ratings** at  $T_a = 25^\circ\text{C}$

Parameter	Symbol	Conditions	Ratings	Unit
Supply voltage	$V_{CC}$ max		14	V
Allowable power dissipation	$P_d$ max	Independent IC	2.0	W
		Mounted on specified board. *	0.8	W
Maximum output current	$I_O$ max	Each output for H bridge, channel 1 to 4.	1	A
Maximum input voltage	$V_{INB}$		13	V
MUTE pin voltage	$V_{MUTE}$		13	V
Operating temperature	$T_{opr}$		-30 to +85	$^\circ\text{C}$
Storage temperature	$T_{stg}$		-55 to +150	$^\circ\text{C}$

\* Specified board size : 76.1×114.3×1.6mm<sup>3</sup>, glass epoxy.

**Recommended Operating Conditions** at  $T_a = 25^\circ\text{C}$

Parameter	Symbol	Conditions	Ratings	Unit
Supply voltage	$V_{CC}$		5.6 to 13	V

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# LA6560

**Electrical Characteristics** at  $T_a = 25^\circ\text{C}$ ,  $V_{CC1} = V_{CC2} = 8\text{V}$ ,  $V_{REF} = 2.5\text{V}$ , unless especially specified.

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
<b>ALL Blocks</b>						
No-load current drain ON	$I_{CC-ON}$	BTL-AMP output ON, LOADING block OFF *1		30	50	mA
No-load current drain OFF	$I_{CC-OFF}$	All outputs OFF *1		10	15	mA
Thermal shutdown temperature	TSD	Design guarantee value	150	175	200	$^\circ\text{C}$
<b>VREF AMP</b>						
VREF-AMP offset voltage	VREF-OFFSET		-10		10	mV
VREF Input voltage range	VREF-IN		1		$V_{CC}-1.5$	V
VREF-OUT output current	I-VREF-OUT	CH1 input reference voltage	2	5	6.6	mA
<b>BTL AMP Block (CH1 to CH4)</b>						
Output offset voltage	$V_{OFF}$	Voltage difference between outputs for BTL AMP, each channel. *2	-50		50	mV
Input voltage range	$V_{IN}$	Input voltage range for input for OP-AMP.	0		$V_{CC}-1.5$	mA
Output voltage	$V_O$	Each voltage between $V_{O+}$ and $V_{O-}$ when $R_L = 8\Omega$ . *3	5.7	6.2		V
Closed-circuit voltage gain	VG	Input and output gain. Input OP-AMP:BUFFER	3.6	4	4.4	Times
Slew rate	SR	AMP Independent Multiply 2 between outputs.		0.5		V/ $\mu\text{s}$
MUTE ON voltage	VMUTE-ON	Output ON voltage, each MUTE *4	2			V
MUTE OFF voltage	VMUTE-OFF	Output OFF voltage, each MUTE *4			0.5	V
<b>Input AMP Block (CH1 to 4)</b>						
Input voltage range	$V_{IN-OP}$		0		$V_{CC}-1.5$	V
Output current (SINK)	SINK-OP		2			mA
Output current (SOURCE)	SOURCE-OP	*5	300	500		$\mu\text{A}$
Output offset voltage	$V_{OFF-OP}$		-10		10	mV
CH1 input changeover voltage 1	VSW-OP1	CH1 input AMP(B), external VREF select *6	2			V
CH1 input changeover voltage 2	VSW-OP2	CH1 input AMP(A), internal VREF select *6			0.5	V
<b>Loading Block (CH5, H bridge)</b>						
Output voltage	$V_{O-LOAD}$	At forward and reverse rotation, $R_L = 8\Omega$ , $V_{CONT}=V_{CC}$ *3	5.7	6.5		V
Break output saturation voltage	$V_{CE-BREAK}$	Output voltage at braking *7			0.3	V
Input low level	$V_{IN-L}$				1	V
Input high level	$V_{IN-H}$		2			V
<b>Power Supply Block (PNP transistor : 2SB632K-use)</b>						
5V supply voltage	$V_{OUT}$	$I_O = 200\text{mA}$	4.8	5.0	5.2	V
REG-IN SINK current	REG-IN-SINK	Base current of external PNP *8	5	10		mA
Line regulation	$\Delta V_{OLN}$	$6\text{V} \leq V_{CC} \leq 12\text{V}$ , $I_O = 200\text{mA}$		10	100	mV
Load regulation	$\Delta V_{OLD}$	$5\text{mA} \leq I_O \leq 200\text{mA}$		10	100	mV

Note \*1 : Current dissipation that is a sum of  $V_{CC1}$  and  $V_{CC2}$  at no load.

\*2 : Input AMP is a BUFFER AMP.

\*3 : Voltage difference between both ends of load ( $8\Omega$ ). Output saturated.

\*4 : Output ON with MUTE : [H] and OFF with MUTE : [L] (HI impedance).

\*5 : The source of input OP-AMP is a constant current. As the  $11\text{k}\Omega$  resistance to the next stage is a load, pay due attention when setting the input OP-AMP gain.

\*6 : With  $V_{IN1-SW}$  : [L], the input AMP selects AMP-A while VREF selects internal VREF ( $\approx 2.5\text{V}$ ).

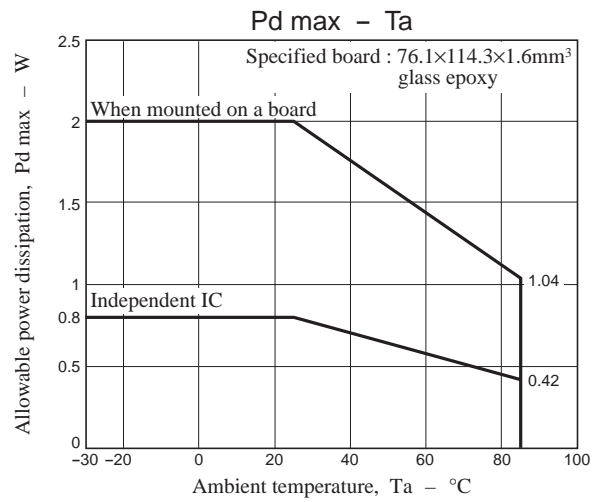
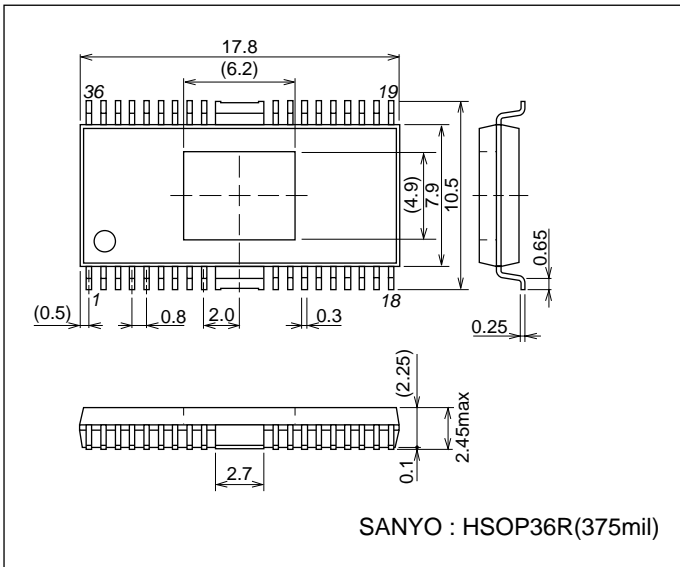
With  $V_{IN1-SW}$  : [H], the input AMP selects AMP-B while VREF selects external VREF ( $\approx V_{REF-IN}$ ).

\*7 : Short (GND) brake used. SINK side output ON.

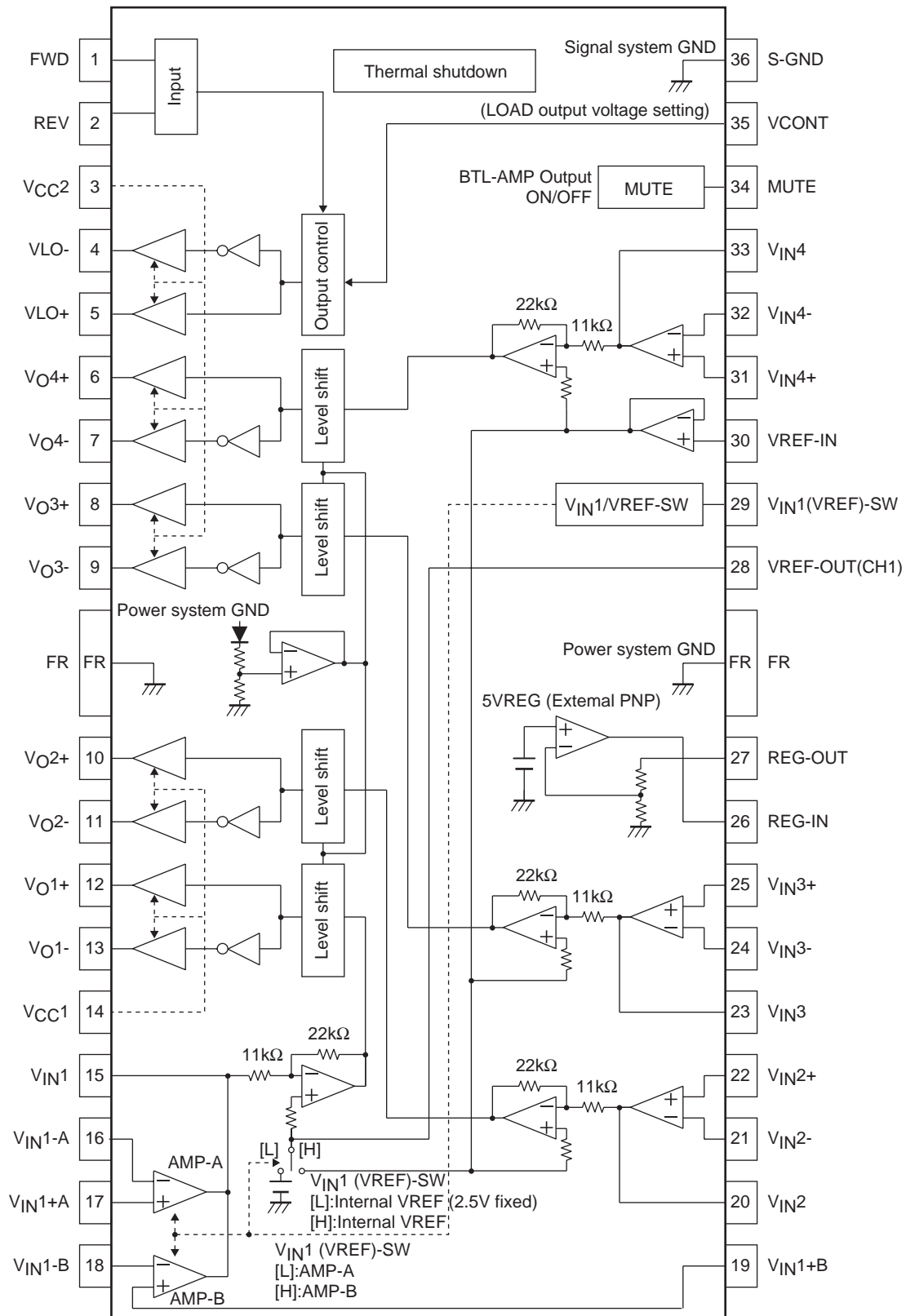
\*8 : 5VREG incorporates a drooping protection circuit and operated when the base current is  $10\text{mA}$  (TYP).

Package Dimensions

unit : mm (typ)  
3251



Block Diagram



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## Pin Functions

Pin No.	Symbol	Pin descriptions
1	FWD	Output change pin (FWD) for 5CH (VLO), logic input for loading block.
2	REV	Output change pin (REV) for 5CH (VLO), logic input for loading block.
3	V <sub>CC2</sub>	Power supply for CH3, 4, and 5.
4	VLO-	Loading output (-)
5	VLO+	Loading output (+)
6	V <sub>O4+</sub>	Output pin (+) for channel 4
7	V <sub>O4-</sub>	Output pin (-) for channel 4
8	V <sub>O3+</sub>	Output pin (+) for channel 3
9	V <sub>O3-</sub>	Output pin (-) for channel 3
10	V <sub>O2+</sub>	Output pin (+) for channel 2
11	V <sub>O2-</sub>	Output pin (-) for channel 2
12	V <sub>O1+</sub>	Output pin (+) for channel 1
13	V <sub>O1-</sub>	Output pin (-) for channel 1
14	V <sub>CC1</sub>	Power supply for CH1, 2 (BTL).
15	V <sub>IN1</sub>	Input pin for channel 1
16	V <sub>IN1-A</sub>	OP-AMP input AMP-A input pin (-)
17	V <sub>IN1+A</sub>	OP-AMP input AMP-A input pin (+)
18	V <sub>IN1-B</sub>	Input AMP-B input pin (-) for channel 1
19	V <sub>IN1+B</sub>	Input AMP-B input pin (+) for channel 1
20	V <sub>IN2</sub>	Input pin for channel 2, input AMP output
21	V <sub>IN2-</sub>	Input pin (-) for channel 2
22	V <sub>IN2+</sub>	Input pin (+) for channel 2
23	V <sub>IN3</sub>	Input pin for channel 3, input AMP output
24	V <sub>IN3-</sub>	Input pin (-) for channel 3
25	V <sub>IN3+</sub>	Input pin (+) for channel 3
26	REG-IN	PNP transistor base connected
27	REG-OUT	5V power output to which the PNP transistor collector connected.
28	VREF-OUT	CH1 reference voltage output. Outputs internal VREF (2.5V : TYP) or external VREF.
29	V <sub>IN1</sub> (VREF) -SW	Pin for changeover between input AMP-A/internal VREF (TYP2.5V) and input AMP-B/ external VREF.
30	VREF-IN	Reference voltage applied pin
31	V <sub>IN4+</sub>	Input pin (+) for channel 4
32	V <sub>IN4-</sub>	Input pin (-) for channel 4
33	V <sub>IN4</sub>	Input pin for channel 4, input AMP output
34	MUTE	All BTL AMP output ON/OFF
35	VCONT	LOADING output voltage setting
36	S-GND	Signal system GND

Note : Center frame (FR) becomes GND for the power system (P-GND). Set this to the minimum potential together with S-GND.

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## Pin Description

Pin No.	Symbol	Pin function	Description	Equivalent circuit
17 19 16 18 15 22 21 20 25 24 23 32 31 33	$V_{IN1+A}$ $V_{IN1+B}$ $V_{IN1-A}$ $V_{IN1-B}$ $V_{IN1}$ $V_{IN2+}$ $V_{IN2-}$ $V_{IN2}$ $V_{IN3+}$ $V_{IN3-}$ $V_{IN3}$ $V_{IN4-}$ $V_{IN4+}$ $V_{IN4}$	Input (CH1 to 4)	Input pin (CH1 to 4)	
1 2	FWD REV	Input (H bridge)	Logic input pin. By combining H and L of this pin, any one of four modes (forward/reversed/brake/idling) can be selected.	
12 13 10 11 8 9 6 7	$V_{O1+}$ $V_{O1-}$ $V_{O2+}$ $V_{O2-}$ $V_{O3+}$ $V_{O3-}$ $V_{O4+}$ $V_{O4-}$	Output (BTL-AMP)	Output for channel 1 to 4.	
4 5 35	VLO- VLO+ VCONT	Output (H bridge)	H bridge (LOADING) output and LOADING output setting pin	
34	MUTE	MUTE	BTL AMP output, which turns ON/OFF the output, MUTE : H Output OFF MUTE : L Output OFF	

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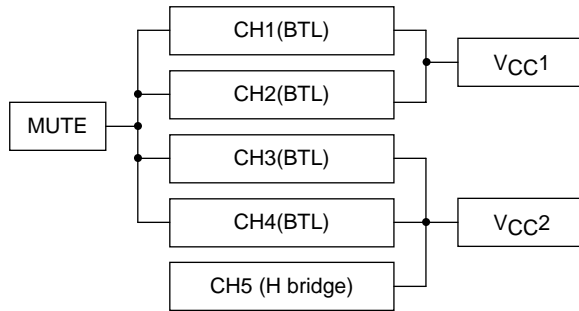
## Truth Table (loading (H bridge) section)

FWD	REV	VLO+	VLO-	Loading output
L	L	OFF	OFF	OFF *1
	H	H	L	Forward
H	L	L	H	Reversed
	H	L	L	(Short) brake *2

\*1 The output has a high impedance.

\*2 At brake, the SINK side transistor is ON (short brake).  
VLO+ and VLO- are approximately on the GND level.

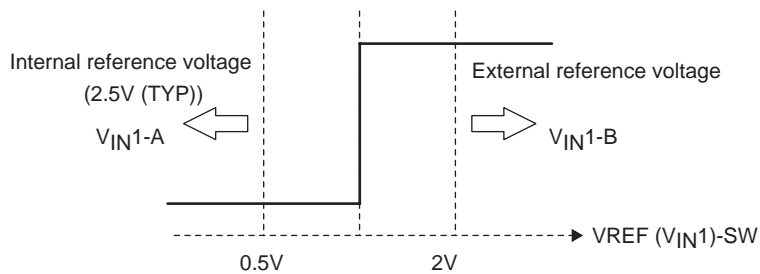
## Relation of MUTE and Power (VCC\*)



## V<sub>IN1</sub> (VREF)-SW (CH1 input AMP selection and internal/external VREF selection function)

(Relation between input AMP (CH1 only) and VREF)

V <sub>IN1</sub> _SW	Input AMP (CH1) state	VREF state
H	V <sub>IN1</sub> -A (AMP-A)	Internal VREF (2.5V : TYP)
L	V <sub>IN1</sub> -B (AMP-B)	External VREF

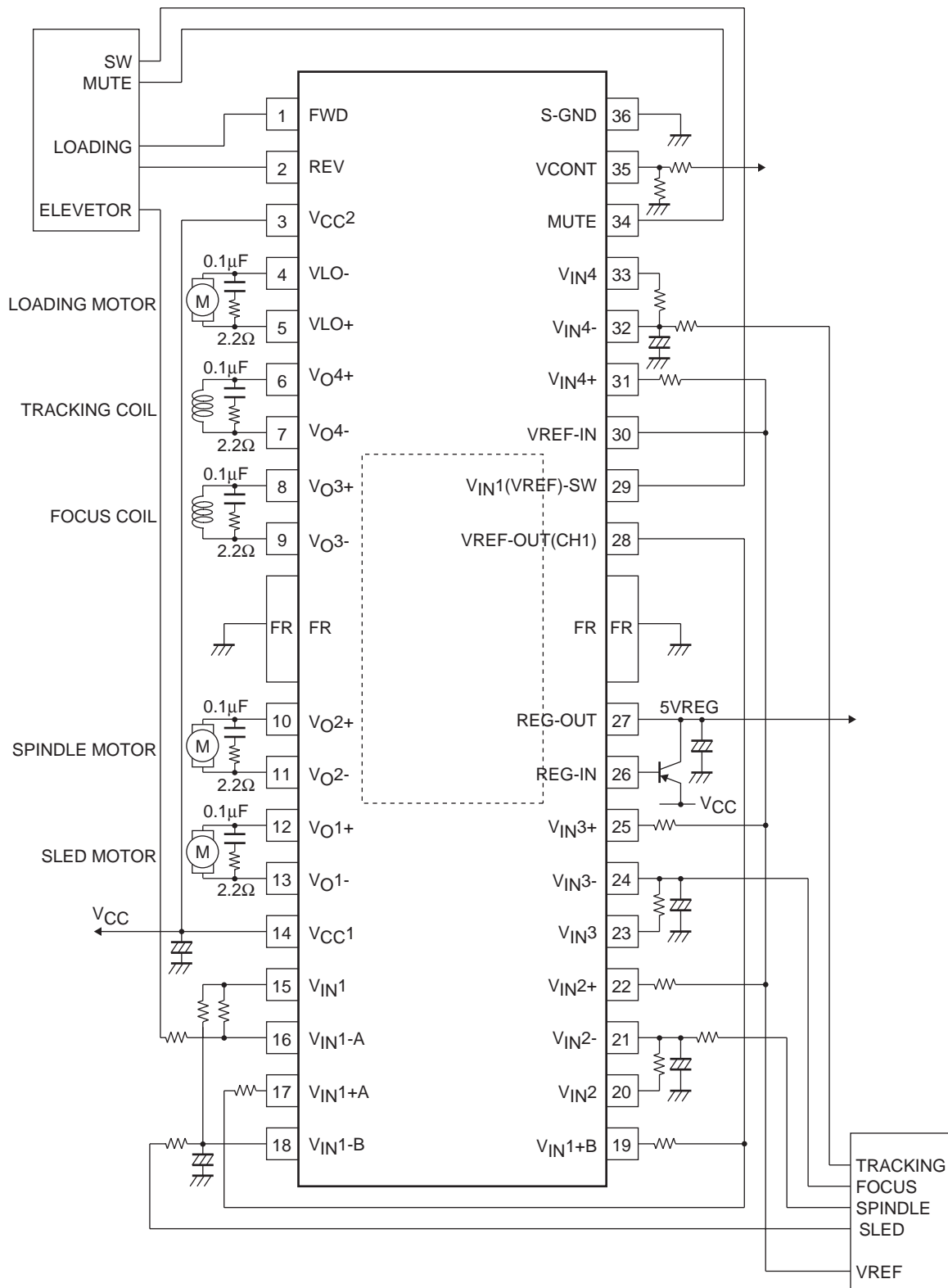


## On MUTE

MUTE	BTLAMP output	VREF-OUT
L	OFF	
H	ON	

VREF-OUT operates in an interlock with MUTE.

Sample Application Circuit





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